

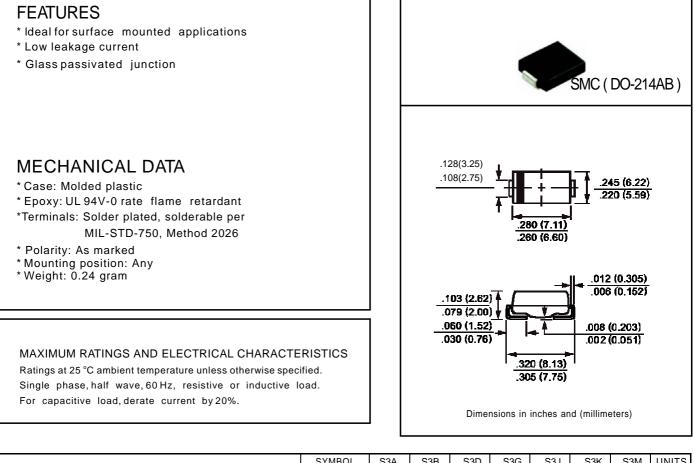
HITANO ENTERPRISE CORP.

S3A THRU S3M

TECHNICAL SPECIFICATIONS OF SURFACE MOUNT SILICON RECTIFIER

VOLTAGE RANGE - 50 to 1000 Volts

CURRENT - 3.0 Amperes



	SYMBOL	S3A	S3B	S3D	S3G	S3J	S3K	S3M	UNITS
Maximum Recurrent Peak Reverse Voltage	Vrrm	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	Vrms	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	VDc	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Rectified Current TA = 75°C	о	3.0							Amps
Peak Forward Surge Current IFM(surge): 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	100							Amps
Maximum Forward Voltage at 3.0A DC	Vf	1.2						Volts	
Maximum DC Reverse Current at $@TA = \frac{25^{\circ}C}{25^{\circ}C}$ Rated DC Blocking Voltage $@TA = 125^{\circ}C$	- Ir	5.0 250							uAmps
Maximum Reverse Recovery Time (Note 3)	trr	2.5							uSec
Typical Thermal Resistance (Note 2)	RθJL	10						°C/W	
Typical Junction Capacitance (Note 1)	CJ	60							pF
Operating and Storage Temperature Range	TJ, TSTG	-65 to + 175							° C

NOTES : 1. Measured at 1 MHz and applied reverse voltage of 4.0VDC

2. Thermal Resistance (Junction to Ambient), 0.4x0.4in² (10X10mm²)copper pads to each terminal.

3. Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A.

RATING AND CHARACTERISTIC CURVES (S3A THRU S3M)

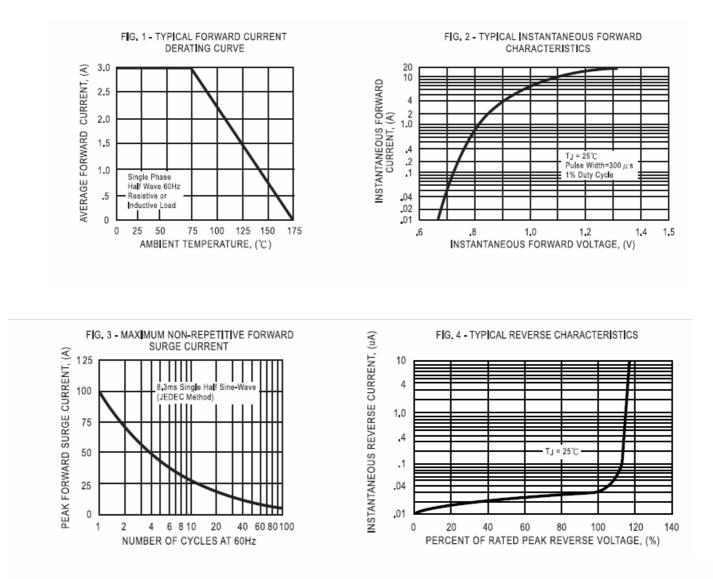


FIG. 5 - TYPICAL JUNCTION CAPACITANCE

